

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1. (Currently amended) A method of fabricating a semiconductor device, comprising the steps of:
 - (a) providing a wafer having a plurality of semiconductor elements formed thereon;
 - (b) affixing a protective tape to a first face of the wafer;
 - (c) grinding a second face of the wafer opposite to the first face;
 - (d) affixing a die bonding film to the second face of the wafer, wherein the die bonding film is affixed by pressing a laminated film of the die bonding film and a separator from the back side of the separator film so that the die bonding film faces the second face of the wafer;
 - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
 - (f) peeling off the protective tape from the first face of the wafer; and
 - (g) dicing the wafer.
2. (Original) The method according to claim 1, wherein the die bonding film contains a thermoplastic resin material.
3. (Original) The method according to claim 1, wherein the first face of the wafer is a face on which the plural semiconductor elements are formed.

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

4. (Original) The method according to claim 1,
wherein the die bonding film functions as an adhesive layer at the time of die-bonding chips obtained by dicing the wafer.
5. (Original) The method according to claim 1, further comprising a step of heating the die bonding film after the step (e) and before the step (f).
6. (Original) The method according to claim 1, further comprising a step of heating the die bonding film after the step (f) and before the step (g).
7. (Original) The method according to claim 1, further comprising, after the step (e) and before the step (f), a step of heating the die bonding film for improving the adherence between the die bonding film and the wafer.
8. (Original) The method according to claim 1, further comprising, after the step (f) and before the step (g), a step of heating the die bonding film for improving the adherence between the die bonding film and the wafer.
9. (Original) The method according to claim 1, further comprising the steps of:
heating the die bonding film to a first temperature after the step (d) and before the step (e); and
heating the die bonding film to a second temperature higher than the first temperature after the step (e) and before the step (f).

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

10. (Original) The method according to claim 1, further comprising the steps of:

heating the die bonding film to a first temperature after the step (d) and before the step (e); and

heating the die bonding film to a second temperature higher than the first temperature after the step (f) and before the step (g).

11. (Original) The method according to claim 1,
wherein, in the step (e), the dicing tape is held by a holding means disposed around the wafer, and

wherein, in the step (g), the wafer affixed to the dicing tape held by the holding means is diced.

12. (Original) The method according to claim 1,
wherein, in the step (c), the wafer is ground to a thickness of not larger than 200 μm .

13. (Currently amended) The method according to claim 1,
wherein in the step (d) ~~comprises the steps of:~~
~~(d1) affixing a laminate~~ the laminated film of the die bonding film and the a
separator film is applied to the second face of the wafer in such a manner that the
die bonding film faces inside; and the step (d) further includes:

~~(d2)~~ peeling off the separator film; and

~~(d3)~~ cutting the die bonding film along an outer periphery of the wafer.

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

14. (Withdrawn) A method of fabricating a semiconductor device, comprising the steps of:
- (a) providing a wafer having a plurality of semiconductor elements formed thereon;
 - (b) affixing a laminate of a die bonding film and a separator film to a back side of the wafer so that the die bonding film faces inside;
 - (c) peeling off the separator film; and
 - (d) cutting the die bonding film along an outer periphery of the wafer.
15. (Withdrawn) The method according to claim 14, wherein the die bonding film contains a thermoplastic resin material.
16. (Withdrawn) The method according to claim 14, wherein the separator film is harder than the die bonding film.
17. (Withdrawn) The method according to claim 14, wherein the die bonding film functions as an adhesive layer at the time of die-bonding chips obtained by dicing the wafer.
18. (Withdrawn) A method of fabricating a semiconductor device, comprising the steps of:
- (a) providing a wafer having a plurality of semiconductor elements formed thereon;
 - (b) affixing a protective tape to a first face of the wafer;

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

- (c) grinding a second face of the wafer opposite to the first face;
- (d) affixing a laminate of a die bonding film and a separator film to the second face of the wafer so that the die bonding film faces inside;
- (e) peeling off the separator film;
- (f) cutting the die bonding film along an outer periphery of the wafer;
- (g) affixing a dicing tape over the die bonding film on the second face of the wafer;
- (h) peeling off the protective tape from the first face of the wafer; and
- (i) dicing the wafer.

19. (Withdrawn) The method according to claim 18,
wherein the die bonding film contains a thermoplastic resin material.

20. (Withdrawn) The method according to claim 18,
wherein the die bonding film functions as an adhesive layer at the time of die-bonding chips obtained by dicing the wafer in the step (i).

21. (Withdrawn) A method of fabricating a semiconductor device,
comprising the steps of:

- (a) providing a wafer having a first face and a second face;
- (b) affixing a protective tape to the first face of the wafer and thinning the wafer from the second face;
- (c) affixing a die bonding film to the second face of the wafer;
- (d) affixing a dicing tape over the die bonding film on the second face of the wafer;

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

- (e) peeling off the protective tape from the first face of the wafer; and
 - (f) dicing the wafer.
22. (New) The method according to claim 1, wherein the protective tape is peeled off from the first face of the wafer after affixing the dicing tape over the die bonding film on the second face of the wafer.
23. (New) The method according to claim 1, wherein the protective tape is peeled off from the first face of the wafer after affixing the die bonding film to the second face of the wafer.
24. (New) The method according to claim 1, wherein said separator film is made of a material selected from the group consisting of polyester and poly (ethylene terephthalate).
25. (New) The method according to claim 24, wherein said die bonding film is made of thermoplastic resin material.
26. (New) The method according to claim 13, wherein the separator film is peeled off prior to said cutting the die bonding film.
27. (New) A method of fabricating a semiconductor device, comprising the steps of:
- (a) providing a wafer having a plurality of semiconductor elements formed thereon;

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

- (b) affixing a protective tape to a first face of the wafer;
 - (c) grinding a second face of the wafer opposite to the first face;
 - (d) affixing a die bonding film to the second face of the wafer;
 - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
 - (f) peeling off the protective tape from the first face of the wafer; and
 - (g) dicing the wafer, and
- further comprising the steps of:
- heating the die bonding film to a first temperature after the step (d) and before the step (e); and
 - heating the die bonding film to a second temperature higher than the first temperature after the step (e) and before the step (f).

28. (New) A method of fabricating a semiconductor device, comprising the steps of:

- (a) providing a wafer having a plurality of semiconductor elements formed thereon;
 - (b) affixing a protective tape to a first face of the wafer;
 - (c) grinding a second face of the wafer opposite to the first face;
 - (d) affixing a die bonding film to the second face of the wafer;
 - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
 - (f) peeling off the protective tape from the first face of the wafer; and
 - (g) dicing the wafer, and
- further comprising the steps of:

Docket No. 501.43182X00]
Appln. No. 10/688,992
August 30, 2005

heating the die bonding film to a first temperature after the step (d) and before the step (e); and

heating the die bonding film to a second temperature higher than the first temperature after the step (f) and before the step (g).